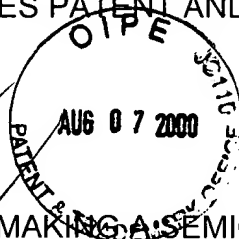


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of :  
Applicants : Rhodes et. al  
Serial No. : 09/008,531  
Filed : 01/16/98  
Title : METHOD OF MAKING A SEMICONDUCTOR DEVICE HAVING  
IMPROVED CONTACTS TO A THIN CONDUCTIVE LAYER  
Docket No. : MIO 0012 V2  
Examiner : EATON  
Art Unit : 2823

Assistant Commissioner of Patents  
Washington, DC 20231



#141C  
T. Yuh  
8-11-00

CERTIFICATE OF MAILING  
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addressed to: Assistant Commissioner for Patents, Washington, D.C.  
20231, on August 3, 2000.

Gregory J. Adams

Reg. No. 44,494

RECEIVED

Sir:

RESPONSE

AUG 10 2000  
TECHNOLOGY CENTER 2800

This paper is being filed in response to the Office Action mailed July 5, 2000.  
Reconsideration of the present application is respectfully requested in light of the  
remarks and amendments below.

IN THE CLAIMS

31. (Amended) A process for making a semiconductor device comprising:  
forming a [layer of conductive material] conductive layer having a topography  
that includes a substantially vertical component;  
forming a contact disposed adjacent to and contacting said vertical component;  
and  
forming a structure having an opening therein under said conductive layer and  
filling said opening with said conductive material to form said vertical component.

40. (New) A process for making a semiconductor device comprising:  
forming a conductive layer having a thick region; and  
forming a contact physically in contact with the thick region.

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108.00 GP  
234.00 GP  
01 FC:103  
02 FC:102